



#### 60V PNP LOW VCE(SAT) TRANSISTOR IN SOT223

#### Description

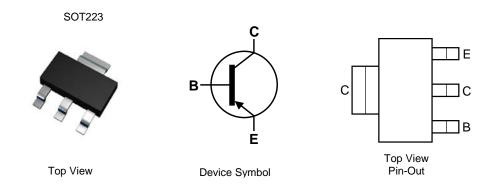
This bipolar junction transistor (BJT) is designed to meet the stringent requirements of automotive applications.

#### Features

- Ideally Suited for Automated Assembly Processes
- Ultra Low Collector-Emitter Saturation Voltage
- Complementary NPN Type Available (DSS60601MZ4Q)
- Ideal for Medium Power Switching or Amplification Applications
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

#### **Mechanical Data**

- Case: SOT223
- Case Material: Molded Plastic. "Green" Molding Compound.
- UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 3
- Weight: 0.112 grams (Approximate)



#### Ordering Information (Notes 4 and 5)

Product	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
DSS60600MZ4Q-13	Automotive	ZPS66	13	12	2500

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/.

5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

#### **Marking Information**

Notes:





ZPS66 = Product Type Marking Code YWW = Date Code Marking Y = Last Digit of Year (ex: 8 = 2018) WW = Week Code 01 - 52



#### Absolute Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	-100	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-60	V
Emitter-Base Voltage	V <sub>EBO</sub>	-7	V
Continuous Collector Current	I <sub>C</sub>	-6	A
Peak Pulse Current	I <sub>CM</sub>	-12	A

### Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Power Dissipation	(Note 6)	Р	1.2	W
	(Note 7)	PD	2.0	W
Thermal Desistance Junction to Ambient	(Note 6)	D	104	°C/W
Thermal Resistance, Junction to Ambient	(Note 7)	R <sub>OJA</sub>	62.5	°C/W
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

# ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge—Human Body Model	ESD HBM	4000	V	3A
Electrostatic Discharge—Machine Model	ESD MM	400	V	С

Notes:

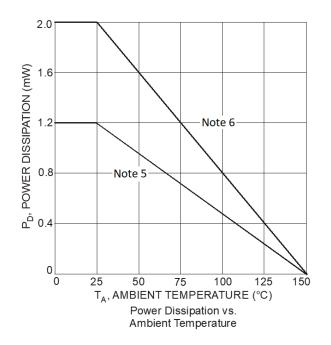
6. Device mounted on FR-4 PCB with minimum recommended pad layout.

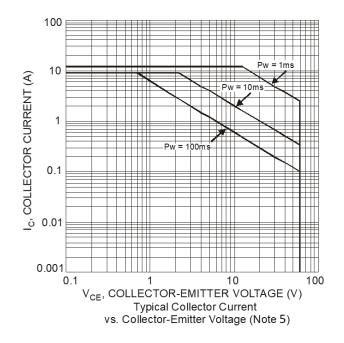
Device mounted on Polymide PCB with 330mm<sup>2</sup> 2oz. Copper pad layout.
Refer to JEDEC specification JESD22-A114 and JESD22-A115.

DSS60600MZ4Q Document Number DS41535 Rev. 1 - 2



# Thermal Characteristics and Derating Information







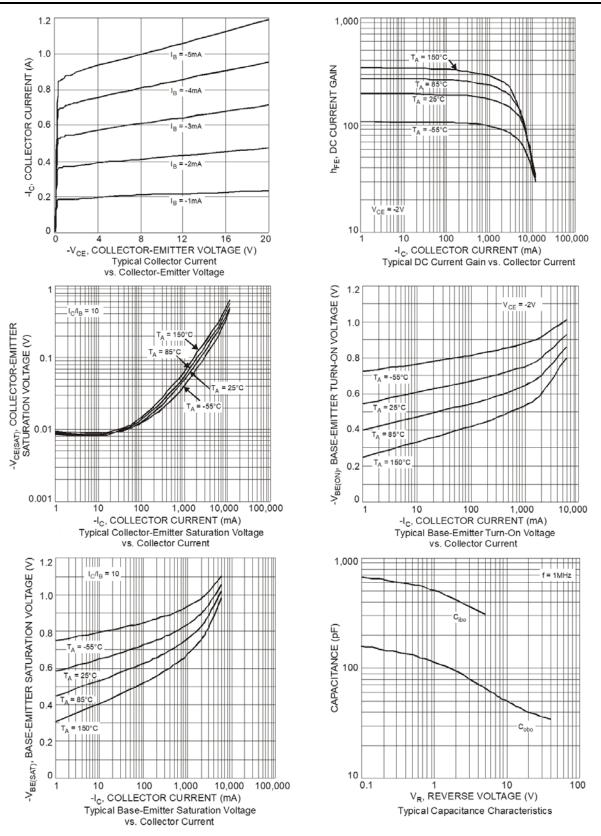
### Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Conditions
OFF CHARACTERISTICS						1
Collector-Base Breakdown Voltage	V <sub>(BR)CBO</sub>	-100	—	—	V	I <sub>C</sub> = -100μA
Collector-Emitter Breakdown Voltage (Note 9)	V <sub>(BR)CEO</sub>	-60	—	—	V	I <sub>C</sub> = -10mA
Emitter-Base Breakdown Voltage	V <sub>(BR)EBO</sub>	-7	_	_	V	I <sub>E</sub> = -100μA
Collector-Base Cutoff Current		_	_	-100	nA	$V_{CB} = -100V, I_E = 0$
	I <sub>СВО</sub>	—	_	-50	μA	$V_{CB} = -100V, I_E = 0, T_A = 150^{\circ}C$
Emitter-Base Cutoff Current	I <sub>EBO</sub>	_	_	-100	nA	$V_{EB} = -6V, I_{C} = 0$
ON CHARACTERISTICS (Note 9)						
		150	_	_		$V_{CE} = -2V, I_{C} = -0.5A$
DC Current Gain	h	120	_	360		$V_{CE} = -2V, I_{C} = -1A$
De culterit Gain	h <sub>FE</sub>	100	_	—		$V_{CE} = -2V, I_{C} = -2A$
		70	—	—		$V_{CE} = -2V, I_{C} = -6A$
		—	_	-50		$I_{C} = -0.1A, I_{B} = -2mA$
		—	-50	-70		$I_{C} = -1A, I_{B} = -100mA$
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>	—	-90	-120	mV	$I_{C} = -2A, I_{B} = -200mA$
		—	—	-250		$I_{C} = -3A, I_{B} = -60mA$
		_	_	-350		$I_{\rm C} = -6A, I_{\rm B} = -600 {\rm mA}$
Equivalent On-Resistance	R <sub>CE(SAT)</sub>	—	45	60	mΩ	$I_{C} = -2A, I_{B} = -200mA$
Base-Emitter Saturation Voltage	V <sub>BE(SAT)</sub>	_	_	-1.0	V	$I_{\rm C} = 1$ A, $I_{\rm B} = -100$ mA
Base-Emitter Turn-on Voltage	V <sub>BE(ON)</sub>	—	_	-0.9	V	$V_{CE} = -2V, I_{C} = -1A$
SMALL SIGNAL CHARACTERISTICS						
Transition Frequency	f⊤	100	-	_	MHz	$V_{CE} = -10V, I_C = -100mA, f = 100MHz$
Output Capacitance	C <sub>obo</sub>	_	50	_	pF	V <sub>CB</sub> = -10V, f = 1MHz
Input Capacitance	Cibo	_	300	_	pF	V <sub>EB</sub> = -5V, f = 1MHz
SWITCHING CHARACTERISTICS						
Turn-On Time	t <sub>on</sub>	—	350	_	ns	
Delay Time	t <sub>d</sub>	_	180	_	ns	V <sub>CC</sub> = -30V, I <sub>C</sub> = -750mA, I <sub>B1</sub> = -15mA
Rise Time	tr	_	170	—	ns	1B1 = - 12111A
Turn-Off Time	t <sub>off</sub>	_	400	—	ns	)/ <u>20)/</u> 750m/
Storage Time	ts	_	300	—	ns	$V_{CC} = -30V, I_C = -750mA,$
Fall Time	tf	_	100	_	ns	$I_{B1} = -I_{B2} = -15mA$

Note: 9. Measured under pulsed conditions. Pulse width  $\leq$  300 µs. Duty cycle  $\leq$  2%

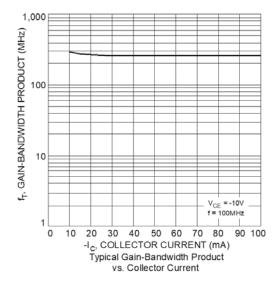


#### Typical Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)





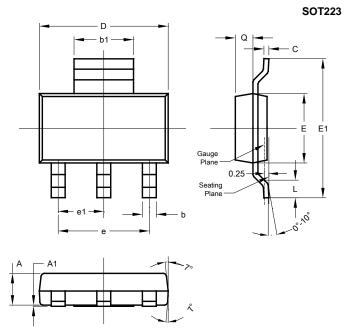
# Typical Electrical Characteristics (continued)





### **Package Outline Dimensions**

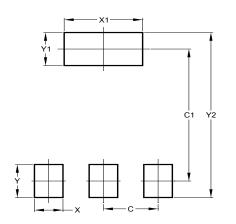
Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b	0.60	0.80	0.70		
b1	2.90	3.10	3.00		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
Е	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	_	_	4.60		
e1	_	_	2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All Dimensions in mm					

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT223

Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00



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